The DFT calculations are performed using the Vienna ab-initio simulation package (VASP) [1–4] with the PW91 generalized gradient approximation (GGA) [5] and projector augmented wave (PAW) potentials [6,7]. Our previous works have confirmed that a cutoff energy of 380 eV is sufficient to give a well converged system energy [8,9]. We model the growth of wetting Cu<sub>2</sub>O layers on top of a three-atomic-layer Cu substrate. To be consistent with the (5 ×6) CSL Cu<sub>2</sub>O-Cu interface model, the Cu substrate is modeled by a periodically repeated slab with a lateral dimension of 6 Cu lattice constants, whereas the Cu<sub>2</sub>O wetting layer growing atop has a lateral dimension of 5 Cu<sub>2</sub>O lattice constants. The bottom layer of the Cu substrate is kept fixed throughout the relaxation. In the surface normal direction, successive slabs are separated by a vacuum region of at least 11 Å. We used slabs with 1, 2, 3 and 4 Cu<sub>2</sub>O wetting layers. For the largest system we had 416 Cu atoms and 100 O atoms. Considering the large number of atoms, we sampled the Brillouin zone only at the  $\Gamma$ -point for all slabs to have consistent results. This should be adequate because we use a larger surface super cell. Electron smearing is carried out following the Methfessel-Paxton technique [10] with N=1 and  $\sigma$ =0.2. The optimized geometries for the Cu<sub>2</sub>O/Cu structures are shown in Fig. s1.



**Fig. s1**: Minimum-energy structures for (a) one-atomic-layer thick  $Cu_2O$  wetting layer, (b) two-atomic-layer thick  $Cu_2O$  wetting layer, (c) three-atomic-layer thick  $Cu_2O$  wetting layer and (d) four-atomic-layer thick  $Cu_2O$  wetting layer. Gray balls depict the Cu atom in the substrate, blue balls the Cu atoms in  $Cu_2O$  wetting layer and red balls oxygen atoms.

The interface energy  $E_{int}$  is calculated using the following equation

$$E_{int} = E_{tot} - N_{Cu}E_{Cu} - N_{Cu_2O}E_{Cu_2O}$$

where  $E_{tot}$  is the total system energy,  $E_{Cu}$  is the energy of bulk Cu unit cell, and  $E_{Cu_20}$  is the energy of Cu<sub>2</sub>O unit cell.  $N_{Cu}$  is the number of the Cu unit cell in the system and  $N_{Cu_20}$ is the number of Cu<sub>2</sub>O unit cell in the wetting layer. Using this notation, a positive value of  $E_{int}$  indicates that the surface is thermodynamically unstable towards dissociation into bulk Cu and Cu<sub>2</sub>O.

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